MOSFET – Single, N-Channel, Small Signal, SC-70

30 V, 270 mA

Features

- Low Gate Charge for Fast Switching
- Small Footprint 30% Smaller than TSOP-6
- ESD Protected Gate
- AEC-Q101 Qualified and PPAP Capable NVS4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain	Steady	T _A = 25 °C	I _D	270	mA
Current (Note 1)	State	T _A = 85 °C		200	
Power Dissipation (Note 1)	Steady State	T _A = 25 °C	P_{D}	330	mW
Pulsed Drain Current t =10 μs			I _{DM}	800	mA
Operating Junction and Storage Temperature			T_J , T_{STG}	–55 to 150	°C
Source Current (Body Diode)			Is	270	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Surface mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).

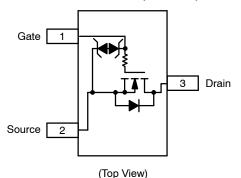


ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} TYP	I _D Max
30 V	1.0 Ω @ 4.0 V	270 mA
	1.5 Ω @ 2.5 V	270 IIIA

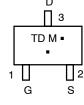
SC-70/SOT-323 (3 LEADS)



MARKING DIAGRAM & PIN ASSIGNMENT



SC-70 / SOT-323 CASE 419 STYLE 8



TD = Device Code

M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTS4001NT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NVS4001NT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

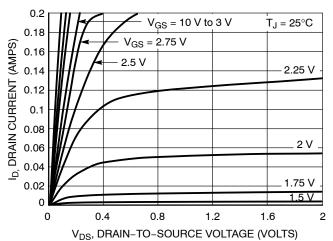
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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition Mi		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•		1		•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 100 μA 30				V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				60		mV/ °C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _E	V _{GS} = 0 V, V _{DS} = 30 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V				±1.0	μΑ
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D}$	= 100 μΑ	0.8	1.2	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-3.4		mV/ °C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.0 V, I _I	_S = 4.0 V, I _D = 10 mA		1.0	1.5	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 10 \text{ mA}$			1.5	2.0	
Forward Transconductance	9FS	V _{DS} = 3.0 V, I _D = 10 mA			80		mS
CHARGES AND CAPACITANCES							
Input Capacitance	C _{ISS}				20	33	pF
Output Capacitance	C _{OSS}	$V_{GS} = 0 \text{ V, f} = 1.0 \text{ MHz,}$ $V_{DS} = 5.0 \text{ V}$			19	32	
Reverse Transfer Capacitance	C _{RSS}				7.25	12	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A			0.9	1.3	nC
Threshold Gate Charge	Q _{G(TH)}				0.2		
Gate-to-Source Charge	Q _{GS}				0.3		
Gate-to-Drain Charge	Q_{GD}				0.2		
SWITCHING CHARACTERISTICS (No	te 3)						
Turn-On Delay Time	td _(ON)	V_{GS} = 4.5 V, V_{DD} = 5.0 V, I_{D} = 10 mA, R_{G} = 50 Ω			17		ns
Rise Time	tr				23		
Turn-Off Delay Time	td _(OFF)				94		
Fall Time	tf				82		
DRAIN-SOURCE DIODE CHARACTE	RISTICS		•				•
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V,	T _J = 25°C		0.65	0.7	V
		I _S = 10 mA	T _J = 125°C		0.43		
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, } dI_{S}/dt = 8.0 \text{ A/}\mu\text{s,}$ $I_{S} = 10 \text{ mA}$			5.0		ns

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

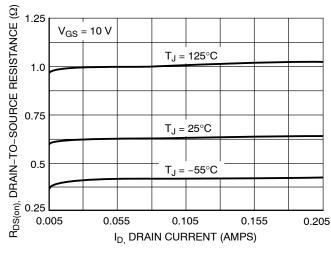
TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



 $V_{DS} = 5 V$ ID, DRAIN CURRENT (AMPS) 0.08 0.06 $T_J = 125^{\circ}C$ 0.04 0.02 $T_J = -55^{\circ}C$ 1.2 1.6 1.4 1.8 2 2.2 1 V_{GS}, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



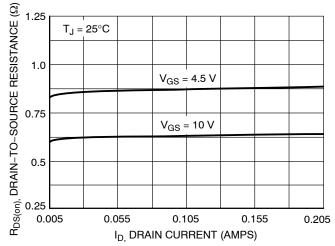
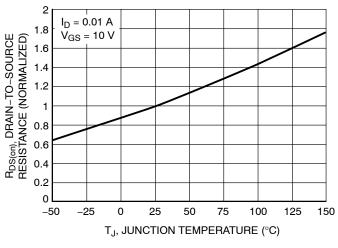


Figure 3. On-Resistance vs. Drain Current and Temperature

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



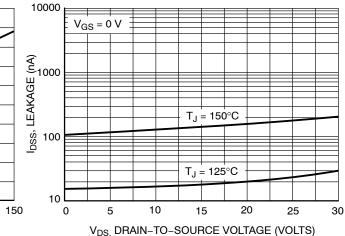
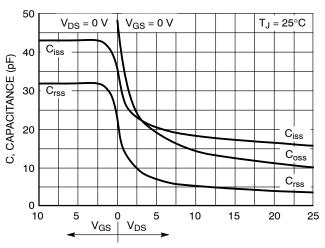
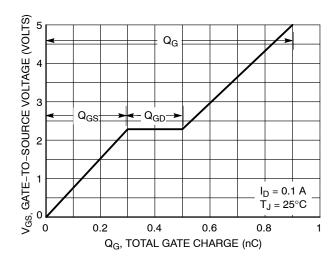


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ unless otherwise noted)





GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

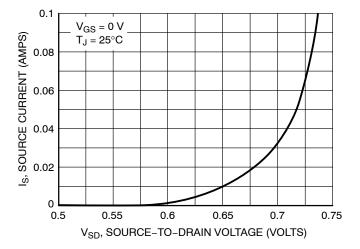
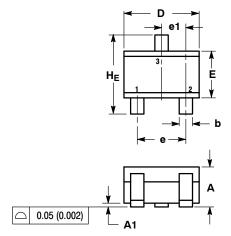


Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04



ISSUE N

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

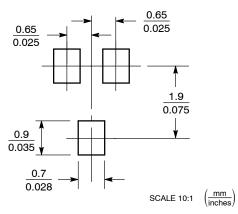
NOTES:

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BSC			
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	

A2 A2

STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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